

CMOS 8-Bit Microcontroller TMP88PS34NG/FG

The TMP88PS34 is the high-speed and high performance 8-bit signal chip microcomputers which built in a program storage area (64 Kbytes), an OSD font storage area (42 Kbytes) and the One-Time PROM of vector table storage area (256 bytes). The TMP88PS34 is pin compatible with the TMP88CS34. The operation possible with the TMP88PS34 can be performed by writing programs to PROM. The TMP88PS34 can write and verify in the same way as the TC571000D an EPROM programmer.

Product No.	OTP	RAM	Package	Adaptor Socket
TMP88PS34NG	64 Kbytes (256 bytes)	1.5 Kbytes	P-SDIP42-600-1.78	BM11174A
TMP88PS34FG	42 Kbytes		P-QFP44-1414-0.80D	BM11175A

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Operational Description

The configuration and function of the TMP88PS34 are the same as those of the TMP88CS34, except in that a one-time PROM is used instead of an on-chip mask ROM.

1. Operation Mode

The TMP88PS34 has two mode: MCU and PROM.

1.1 MCU Mode

The MCU mode is activated by fixing the TEST/VPP pin at low level.
In the MCU mode, operation is the same as with the TMP88CS34.

1.1.1 Program Memory

The TMP88PS34 has a 64 Kbytes (addresses 04000H to 13EFFFH in the MCU mode, addresses 10000H to 1FEFFFH in the PROM mode) of program storage area, 42 Kbyte (addresses 20000H to 2A7FFFH in the MCU mode, addresses 05800H to 0FFFFH in the PROM mode) and 256 byte (addresses FFF00H to FFFFFH in the MCU mode, addresses 1FF00H to 1FFFFH in the PROM mode) one-time PROM of vector table storage area.

1.1.2 Data Memory

The TMP88PS34 has an on-chip 1.5-Kbyte data memory (static RAM).

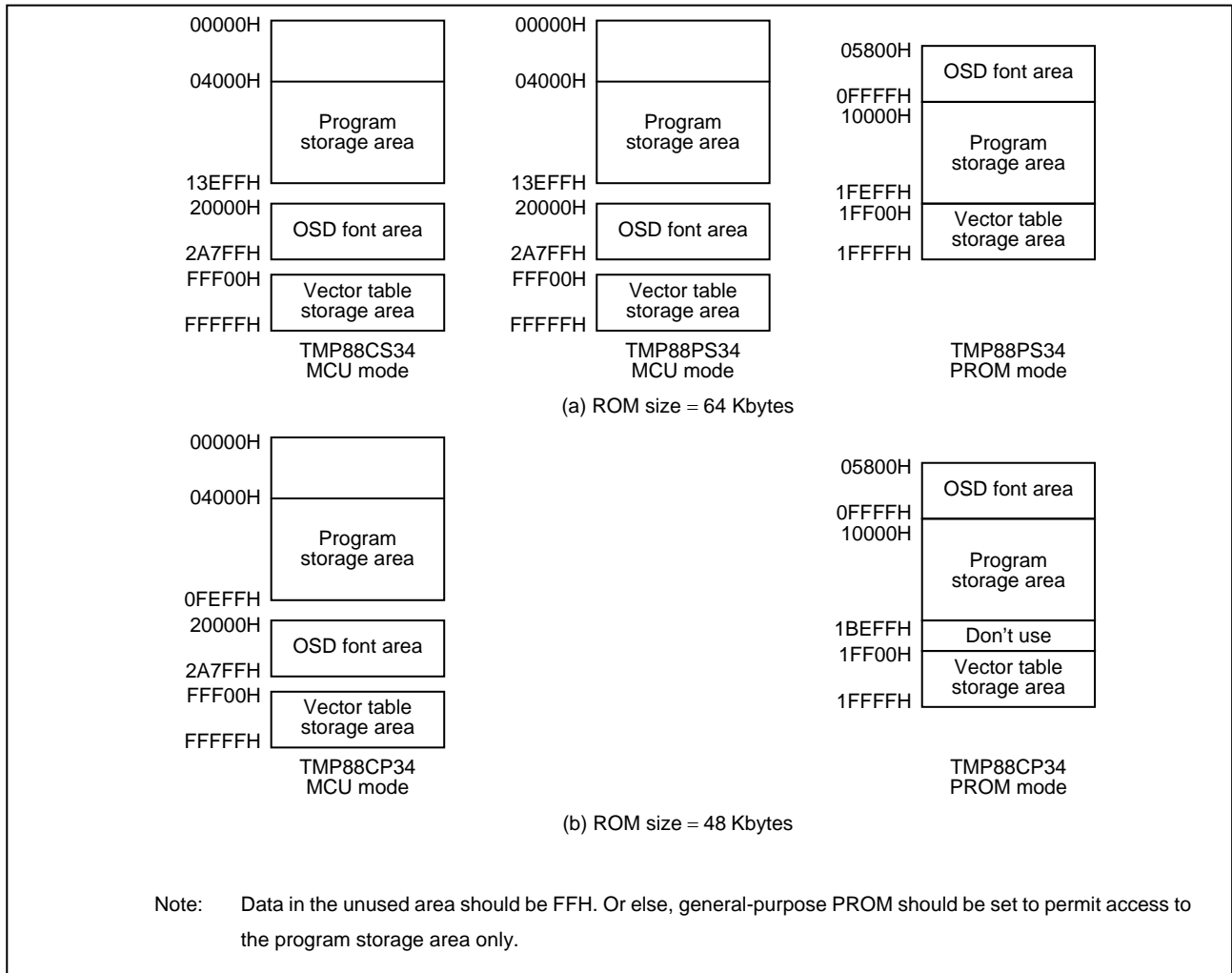


Figure 1.1.1 Program Storage Area

1.1.3 Input/Output Circuit for Pins

(1) Control pins

The TMP88PS34 is identical to the TMP88CS34 and TMP88CP34 except that it has a TEST pin without a pull-down resistor.

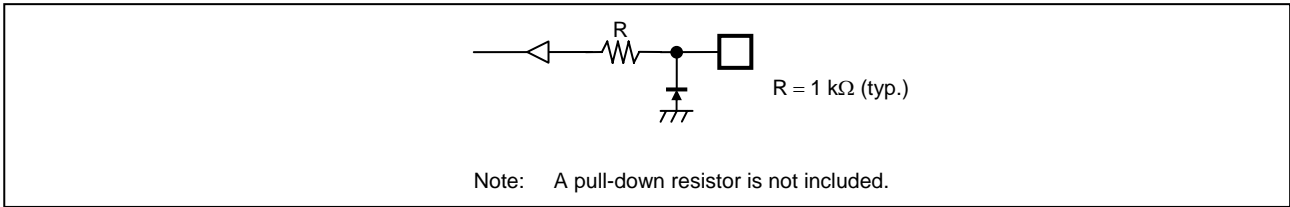


Figure 1.1.2 TEST pin

(2) I/O ports

The input/output circuit for the TMP88PS34 I/O port is the same as that for the TMP88CS34 and TMP88CP34.

1.2 PROM Mode

The PROM mode is used to write and verify programs with a general-purpose PROM programmer. The high-speed programming mode can be used for program operation.

The TMP88PS34 is not supported an electric signature mode, so the ROM type must be set to TC571000D.

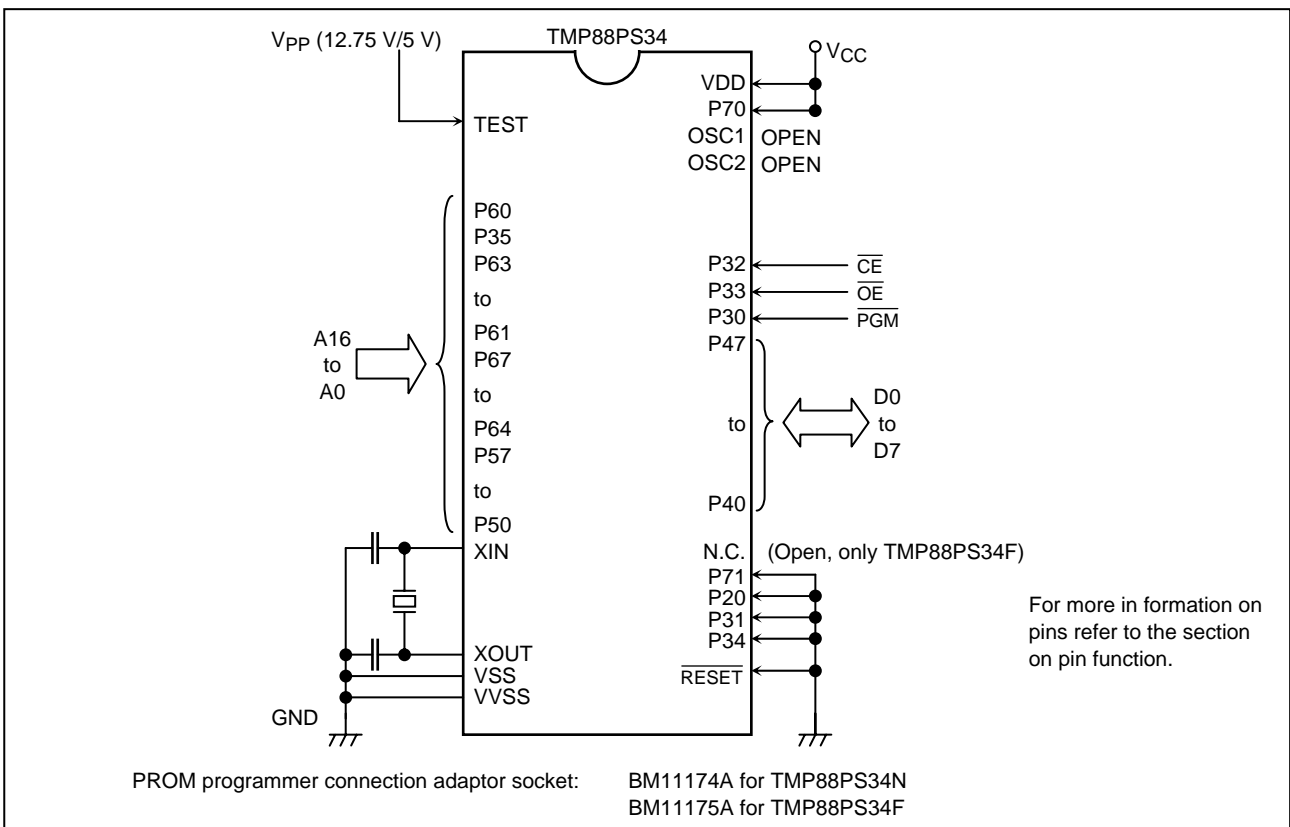


Figure 1.2.1 Setting for PROM Mode

1.3 Programming Flowchart (High-speed Programming Mode)

The high-speed programming mode is achieved by applying the program voltage (+12.75 V) to the VPP pin when $V_{CC} = 6.25$ V. After the address and input data are stable, the data is programmed by applying a single 0.1ms program pulse to the \overline{PGM} input. The programmed data is verified. If incorrect, another 0.1ms program pulse is applied. This process should be repeated (up to 25 times) until the program operates correctly. After that, change the address and input data, and program as before. When programming has been completed, the data in all addresses should be verified with $V_{CC} = V_{PP} = 5$ V.

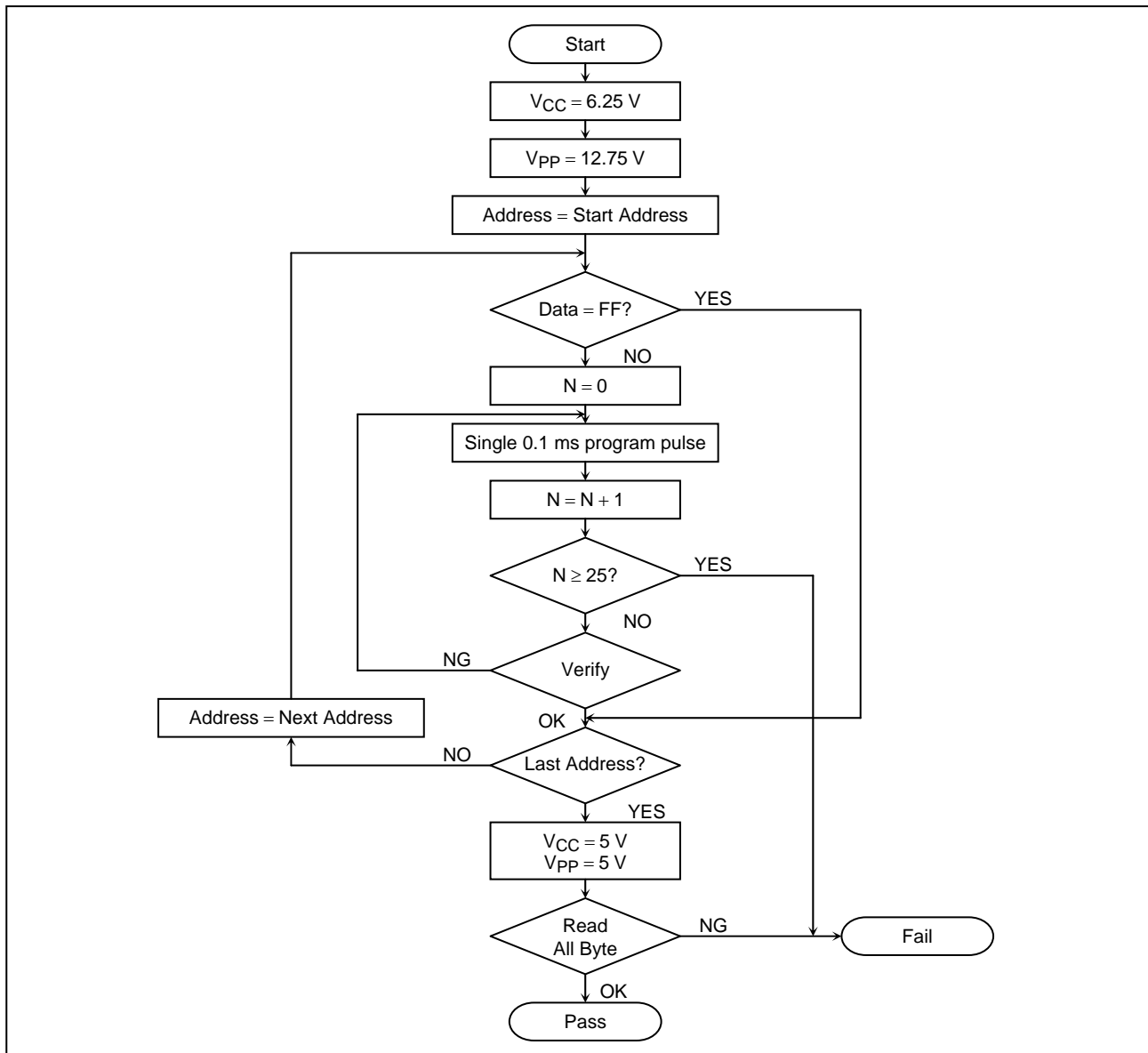


Figure 1.3.1 Flow Chart of High-speed Programming

1.4 Writing Method for General-purpose PROM Program

(1) Adapters

BM11174A: TMP88PS34NG

BM11175A: TMP88PS34FG

(2) PROM programmer specifying

1. PROM type is specified to TC571000D. (Note 1)

Writing voltage: 12.75 V (high-speed program mode)

2. Data transfer (copy) (Note 1)

In the TMP88PS34, EPROM is within the addresses 10000H to 1FEFFH (Program storage area) and 0A000H to 0FFFFH (OSD font area) and 1FF00H to 1FFFFH (Vector table storage area). Data is required to be transferred (copied) to the addresses where it is possible to write. The program area in MCU mode and PROM mode is referred to "Program memory area" in Figure 1.1.1.

3. Writing address is specified. (Note 1)

Start address: 05800H

End address: 1FFFFH

(3) Writing

Writing/Verifying is required to be executed in accordance with PROM programmer operating procedure.

Note 1: The specifying method is referred to the PROM programmer description. Either write the data FF_H to the unused area or set the PROM programmer to access only the program storage area.

Note 2: When MCU is set to an adapter or the adapter is set to PROM programmer, a position of pin 1 must be adjusted. If the setting is reversed, MCU, the adapter and PROM program is damaged.

Input/Output Circuit

(1) Control pins

The input/output circuitries of the TMP88PS34 control pins are shown below.

Control Pin	I/O	Input/Output Circuitry	Remarks
XIN XOUT	I/O		Resonator connection pins (high-frequency) $R_f = 1.2 \text{ M}\Omega$ (typ.) $R_O = 0.5 \text{ k}\Omega$ (typ.)
$\overline{\text{RESET}}$	I/O		Sink open drain output Hysteresis input Pull-up resistor $R_{IN} = 220 \text{ M}\Omega$ (typ.) $R = 1 \text{ k}\Omega$ (typ.)
$\overline{\text{STOP}} / \overline{\text{INT5}}$ (P20)	Input		Hysteresis input $R = 1 \text{ k}\Omega$ (typ.)
TEST	Input		$R = 1 \text{ k}\Omega$ (typ.)
OSC1 OSC2	I/O		$R_f = 1.2 \text{ M}\Omega$ (typ.) $R_O = 0.5 \text{ k}\Omega$ (typ.)

(2) Input/Output ports

Port	I/O	Input/Output Circuitry	Remarks
P20	I/O	<p>Initial "High-Z"</p>	<p>Sink open drain output Hysteresis input</p> <p>R = 1 kΩ (typ.)</p>
P30 to P33, P50, P57, P70, P71	I/O	<p>Initial "High-Z"</p>	<p>Tri-state I/O Hysteresis input</p> <p>R = 1 kΩ (typ.)</p>
P34, P35, P51, P52	I/O	<p>Open drain output enable</p>	<p>Tri-state I/O or Open drain output programmable Hysteresis input</p> <p>R = 1 kΩ (typ.)</p>
P40 to P47	I/O	<p>Initial "High-Z"</p>	<p>Tri-state I/O</p> <p>R = 1 kΩ (typ.)</p>
P53 to P56	I/O	<p>Initial "High-Z"</p>	<p>Tri-state I/O Hysteresis input Key-on wake-up input ($V_{IL4} = 0.65 \times V_{DD}$)</p> <p>R = 1 kΩ (typ.) R_A = 5 kΩ (typ.) C_A = 22 pF (typ.)</p>

Port	I/O	Input/Output Circuitry	Remarks
P60	I/O		<p>Sink open drain I/O High-current output $I_{OL} = 20 \text{ mA (typ.)}$</p> <p>$R = 1 \text{ k}\Omega \text{ (typ.)}$ $R_A = 5 \text{ k}\Omega \text{ (typ.)}$ $C_A = 22 \text{ pF (typ.)}$</p> <p>Key-on wake-up input ($V_{IL4} = 0.65 \times V_{DD}$)</p>
P61	I/O		<p>Tri-state I/O</p> <p>$R = 1 \text{ k}\Omega \text{ (typ.)}$ $R_A = 5 \text{ k}\Omega \text{ (typ.)}$ $C_A = 22 \text{ pF (typ.)}$</p> <p>Key-on wake-up input ($V_{IL4} = 0.65 \times V_{DD}$)</p>
P62 to P67	I/O		<p>Tri-state I/O</p> <p>$R = 1 \text{ k}\Omega \text{ (typ.)}$</p>

Electrical Characteristics

Absolute maximum ratings

(V_{SS} = 0 V)

Parameter	Symbol	Pins	Ratings	Unit
Supply voltage	V _{DD}	–	–0.3 to 6.5	V
Programmable voltage	V _{PP}	TEST/V _{PP} pin	–0.3 to 13.0	
Input voltage	V _{IN}	–	–0.3 to V _{DD} + 0.3	
Output voltage	V _{OUT1}	–	–0.3 to V _{DD} + 0.3	
Output current (Per 1 pin)	I _{OUT1}	Ports P2, P3, P4, P5, P61 to P67, P7	3.2	mA
	I _{OUT2}	Ports P60	30	
Output current (Total)	Σ I _{OUT1}	Ports P2, P3, P4, P5, P61 to P67, P7	30	
	Σ I _{OUT2}	Ports P60	30	
Power dissipation [T _{opr} = 70°C]	PD	–	400	mW
Soldering temperature (time)	T _{sld}	–	260 (10 s)	°C
Storage temperature	T _{stg}	–	–55 to 125	
Operating temperature	T _{opr}	–	–30 to 70	

Note: The absolute maximum ratings are rated values which must not be exceeded during operation, even for an instant. Any one of the ratings must not be exceeded. If any absolute maximum rating is exceeded, a device may break down or its performance may be degraded, causing it to catch fire or explode resulting in injury to the user. Thus, when designing products which include this device, ensure that no absolute maximum rating value will ever be exceeded.

Recommended operating conditions

(V_{SS} = 0 V, T_{opr} = –30 to 70 °C)

Parameter	Symbol	Pins	Conditions	Min	Max	Unit
Supply voltage	V _{DD}	–	fc = 16 MHz NORMAL mode	4.5	5.5	V
			fc = 16 MHz IDLE mode			
			– STOP mode			
Input high voltage	V _{IH1}	Except hysteresis input	V _{DD} = 4.5 to 5.5V	V _{DD} × 0.70	V _{DD}	V
	V _{IH2}	Hysteresis input		V _{DD} × 0.75		
	V _{IH3}	Key-on Wake-up input		V _{DD} × 0.90		
Input low voltage	V _{IL1}	Except hysteresis input	V _{DD} = 4.5 to 5.5V	0	V _{DD} × 0.30	V
	V _{IL2}	Hysteresis input			V _{DD} × 0.25	
	V _{IL3}	Key-on Wake-up input			V _{DD} × 0.65	
Clock frequency	fc	XIN, XOUT	V _{DD} = 4.5 to 5.5V	8.0	16.0	MHz
	f _{OSC}	Internal clock	V _{DD} = 4.5 to 5.5V	fc = 8 MHz 8.0	12.0	
				fc = 16 MHz 16.0	24.0	

Note 1: The recommended operating conditions for a device are operating conditions under which it can be guaranteed that the device will operate as specified. If the device is used under operating conditions other than the recommended operating conditions (supply voltage, operating temperature range, specified AC/DC values etc.), malfunction may occur. Thus, when designing products which include this device, ensure that the recommended operating conditions for the device are always adhered to.

Note 2: Clock frequency fc: Supply voltage range is specified in NORMAL mode and IDLE mode.

Note 3: Smaller value is alternatively specified as the maximum value.

DC Characteristics

(V_{SS} = 0 V, T_{opr} = -30 to 70 °C)

Parameter	Symbol	Pins	Conditions	Min	Typ.	Max	Unit
Hysteresis voltage	V _{HS}	Hysteresis input		-	0.9	-	V
Input current	I _{IN1}	TEST	V _{DD} = 5.5 V, V _{IN} = 5.5 V/0 V	-	-	±2	μA
	I _{IN2}	Open drain ports	V _{DD} = 5.5 V, V _{IN} = 5.5 V/0 V	-	-	±2	
	I _{IN3}	Tri-state ports	V _{DD} = 5.5 V, V _{IN} = 5.5 V/0 V	-	-	±2	
	I _{IN4}	RESET, STOP	V _{DD} = 5.5 V, V _{IN} = 5.5 V/0 V	-	-	±2	
Input resistance	R _{IN2}	RESET	V _{DD} = 5.5 V, V _{IN} = 0 V	100	220	450	kΩ
Output leakage current	I _{LO1}	Sink open drain ports	V _{DD} = 5.5 V, V _{OUT} = 5.5 V	-	-	2	μA
	I _{LO2}	Tri-state ports	V _{DD} = 5.5 V, V _{OUT} = 5.5 V/0 V	-	-	±2	
Output high voltage	V _{OH2}	Tri-state ports	V _{DD} = 4.5 V, I _{OH} = -0.7 mA	4.1	-	-	V
Output low voltage	V _{OL}	Except XOUT and ports P60	V _{DD} = 4.5 V, I _{OL} = 1.6 mA	-	-	0.4	
Output low current	I _{OL3}	Port P60	V _{DD} = 4.5 V, V _{OL} = 1.0 V	-	20	-	mA
Supply current in NORMAL mode	I _{DD}	-	V _{DD} = 5.5 V f _c = 16 MHz V _{IN} = 5.3 V/0.2 V (Note3)	-	25	30	
Supply current in IDLE mode				-	20	25	
Supply current in STOP mode			V _{DD} = 5.5 V V _{IN} = 5.3 V/0.2 V	-	0.5	10	μA

Note 1: Typical values show those at T_{opr} = 25 °C, V_{DD} = 5 V.

Note 2: Input Current I_{IN3}; The current through resistor is not included.

Note 3: Supply Current I_{DD}; The current (Typ. 0.5 mA) through ladder resistors of ADC is included in NORMAL mode and IDLE mode.

AD Conversion Characteristics

(V_{SS} = 0 V, V_{DD} = 4.5 V to 5.5 V, T_{opr} = -30 to 70 °C)

Parameter	Symbol	Conditions	Min	Typ.	Max	Unit
Analog reference voltage	V _{AREF}	supplied from V _{DD} pin.	-	V _{DD}	-	V
	V _{ASS}	supplied from V _{SS} pin.	-	0	-	
Analog reference voltage range	ΔV _{AREF}	= V _{DD} - V _{SS}	-	V _{DD}	-	
Analog input voltage	V _{AIN}		V _{SS}	-	V _{DD}	LSB
Nonlinearity error		V _{DD} = 5.0 V	-	-	±1	
Zero point error			-	-	±2	
Full scale error			-	-	±2	
Total error			-	-	±3	

Note: The total error means all error except quanting error.

AC characteristics

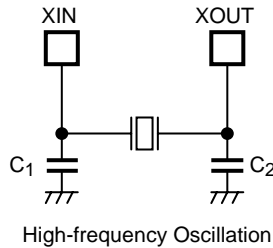
(V_{SS} = 0 V, V_{DD} = 4.5 V to 5.5 V, T_{opr} = -30 to 70 °C)

Parameter	Symbol	Conditions	Min	Typ.	Max	Unit
Machine cycle time	t _{cy}	in NORMAL mode	0.5	-	1.0	μs
		in IDLE mode				
High level clock pulse width	t _{WCH}	For external clock operation (XIN input), f _c = 16 MHz	31.25	-	-	ns
Low level clock pulse width	t _{WCL}					

Recommended oscillating conditions

(V_{SS} = 0 V, V_{DD} = 4.5 V to 5.5 V, T_{opr} = -30 to 70 °C)

Parameter	Oscillator	Oscillation Frequency	Recommended Oscillator	Recommended Constant	
				C ₁	C ₂
High-frequency oscillation	Ceramic resonator	8 MHz	Murata CSA 8.00MTZ	30 pF	30 pF
		16 MHz	Murata CSA 16.00MXZ040	5 pF	5 pF



Note 1: To keep reliable operation, shield the device electrically with the metal plate on its package mold surface against the high electric field, for example, by CRT (Cathode Ray Tube).

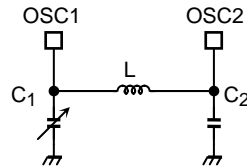
Note 2: The product numbers and specifications of the resonators by Murata Manufacturing Co., Ltd. are subject to change. For up-to-date information, please refer to the following URL;

<http://www.murata.co.jp/search/index.html>

Recommended oscillating conditions

(V_{SS} = 0 V, V_{DD} = 4.5 V to 5.5 V, T_{opr} = -30 to 70 °C)

Item	Resonator	Oscillation Frequency	Recommended parameter value		
			L (μH)	C ₁ (pF)	C ₂ (pF)
Oscillation for OSD	LC resonator	8 MHz	33	5 to 30	10
		12 MHz	15	5 to 30	10
		16 MHz	10	5 to 30	10
		20 MHz	6.8	5 to 25	10
		24 MHz	4.7	5 to 25	10



Oscillation for OSD

The frequency generated in LC oscillation can be obtained using the following equations.

$$f = \frac{1}{2\pi\sqrt{LC}}, C = \frac{C_1 \cdot C_2}{C_1 + C_2}$$

C₁ is not fixed at a constant value. It can be changed to tune into the desired frequency.

Note 1: Toshiba's OSD circuit determines a horizontal display start position by counting clock pulses generated in LC oscillation. For this reason, the OSD circuit may fail to detect clock pulses normally, resulting in the horizontal start position becoming unstable, at the beginning of oscillation, if the oscillation amplitude is low.

Changing L and C₂ from the values recommended for a specific frequency may hamper a stable OSD display.

If the LC oscillation frequency is the same as a high-frequency clock value, the oscillation of the high-frequency oscillator may cause the LC oscillation frequency to fluctuate, thus making OSD displays flicker.

When determining these parameters, please check the oscillation frequency and the stability of oscillation on your TV sets.

Also check the determined parameters on your final products, because the optimum parameter values may vary from one product to another.

Note 2: When using the LSI package in a strong electric field, such as near a CRT, electrically shield the package so that its normal operation can be maintained.

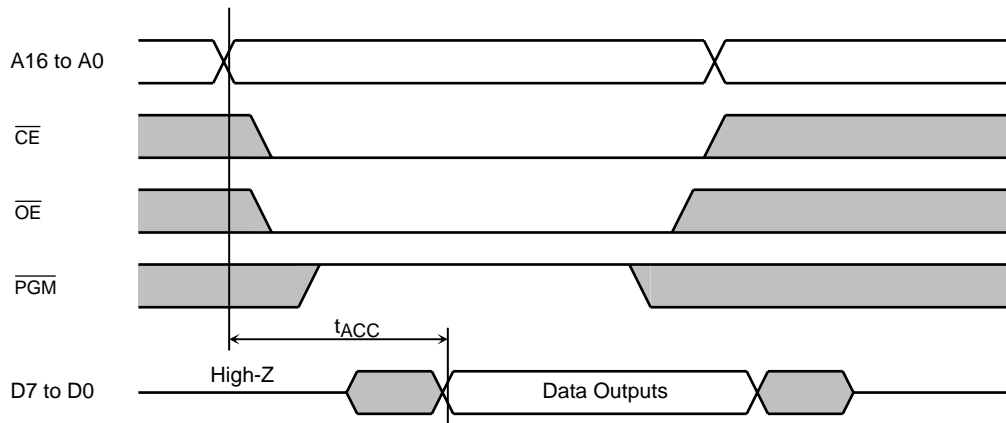
DC/AC Characteristics (PROM mode)

(V_{SS} = 0 V)

(1) Read operation (V_{DD} = 5.0 ± 0.25 V, T_{opr} = 25 ± 5 °C)

Parameter	Symbol	Conditions	Min	Typ.	Max	Unit
Input high voltage (A0 to A16, \overline{CE} , \overline{OE} , \overline{PGM})	V _{IH4}		V _{DD} × 0.7	–	V _{DD}	V
Input low voltage (A0 to A16, \overline{CE} , \overline{OE} , \overline{PGM})	V _{IL4}		0	–	0.8	
Program power supply voltage	V _{PP}		4.75	5.0	5.25	
Address access time	t _{ACC}		–	1.5t _{cyc} + 300	–	ns

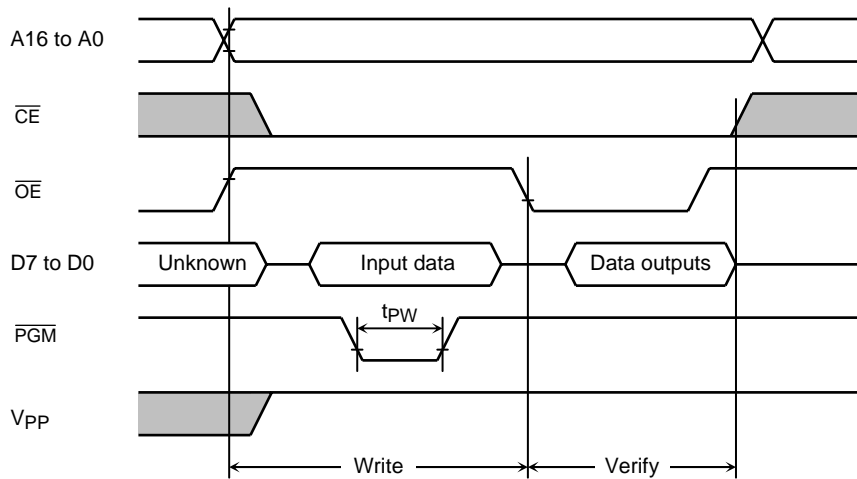
Note: t_{cyc} = 400 ns at 10 MHz



(2) High-speed programming operation (T_{opr} = 25 ± 5 °C, V_{DD} = 6.25 ± 0.25 V)

Parameter	Symbol	Conditions	Min	Typ.	Max	Unit
Input high voltage (D0 to D7, A0 to A16, \overline{CE} , \overline{OE} , \overline{PGM})	V _{IH4}		V _{DD} × 0.7	–	V _{DD}	V
Input low voltage (D0 to D7, A0 to A16, \overline{CE} , \overline{OE} , \overline{PGM})	V _{IL4}		0	–	0.8	
Program power supply voltage	V _{PP}		12.5	12.75	13.0	
Initial program pulse width	t _{PW}	V _{DD} = 6.0 V	0.095	0.1	0.105	ms

High-speed Programming Timing



Note 1: When V_{CC} power supply is turned on or after, V_{PP} must be increased.

When V_{CC} power supply is turned off or before, V_{PP} must be increased.

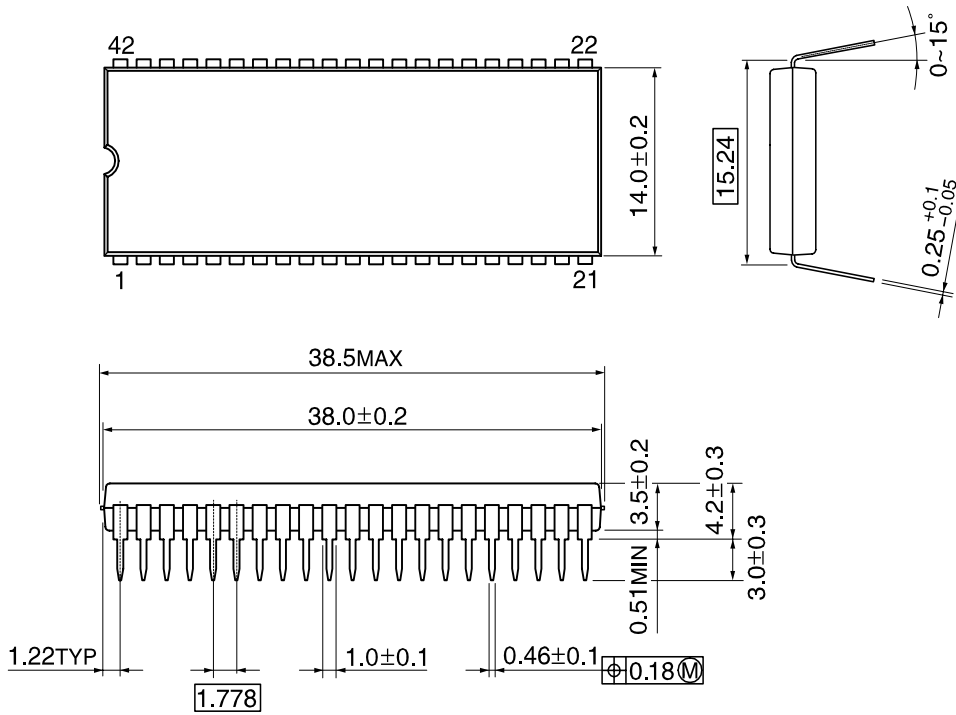
Note 2: The device must not be set to the EPROM programmer or picked up from it under applying the program voltage ($12.75\text{ V} \pm 0.25\text{ V}$) to the V_{PP} pin as the device is damaged.

Note 3: Be sure to execute the Recommended programming mode with the Recommended programming adaptor. If a mode or an adaptor except the above, the misoperation sometimes occurs.

Package

P-SDIP42-600-1.78

Unit: mm



P-QFP44-1414-0.80D

Unit: mm

